

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- High Voltage Transistor

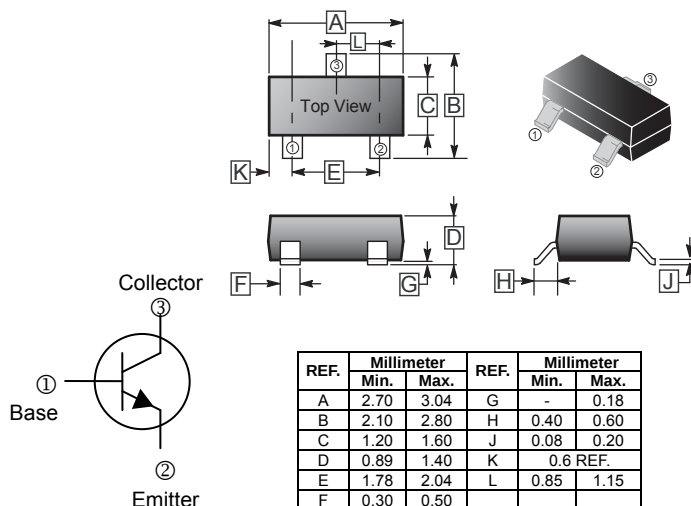
MARKING

3D

PACKING INFORMATION

Package	MPQ	Leader Size
SOT-23	3K	7 inch

SOT-23



MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	400	V
Collector - Emitter Voltage	V _{CEO}	400	V
Emitter - Base Voltage	V _{EBO}	6	V
Collector Current - Continuous	I _C	0.2	A
Collector Current - Pulsed	I _{CM}	0.3	A
Collector Power Dissipation	P _C	350	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	357	°C / W
Junction, Storage Temperature	T _J , T _{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	I _C = 100μA, I _E = 0	V _{(BR)CBO}	400	-	-	V
Collector-Emitter Breakdown Voltage ¹	I _C = 1mA, I _B = 0	V _{(BR)CEO}	400	-	-	V
Emitter-Base Breakdown Voltage	I _E = 10μA, I _C = 0	V _{(BR)EBO}	6	-	-	V
Collector Cut-Off Current	V _{CB} = 400V, I _E = 0	I _{CBO}	-	-	0.1	μA
Emitter Cut-Off Current	V _{EB} = 4V, I _C = 0	I _{EBO}	-	-	0.1	μA
DC Current Gain ¹	V _{CE} = 10V, I _C = 1mA	h _{FE}	40	-	-	
	V _{CE} = 10V, I _C = 10mA		50	-	200	
	V _{CE} = 10V, I _C = 50mA		45	-	-	
	V _{CE} = 10V, I _C = 100mA		40	-	-	
Collector-Emitter Saturation Voltage ¹	I _C = 1mA, I _B = 0.1mA	V _{CE(sat)}	-	-	0.4	V
	I _C = 10mA, I _B = 1mA		-	-	0.5	
	I _C = 50mA, I _B = 5mA		-	-	0.75	
Base-Emitter Saturation Voltage ¹	I _C = 10mA, I _B = 1mA	V _{BE(sat)}	-	-	0.75	V
Output Capacitance	V _{CB} = 20V, I _E = 0, f = 1MHz	C _{obo}	-	-	7	pF
Input Capacitance	V _{EB} = 0.5V, I _C = 0, f = 1MHz	C _{ibo}	-	-	130	pF

Note:

1. Pulse test: pulse width ≤ 300μs, duty cycles ≤ 2.0%.

CHARACTERISTIC CURVES

